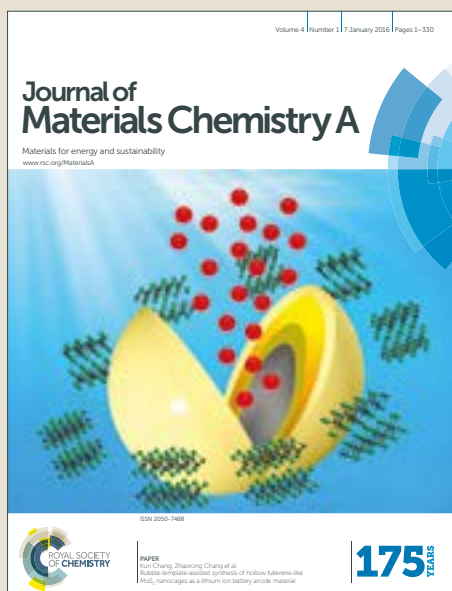


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ARTICLE

6 Asymmetric Supercapacitor with Excellent Cycling Performance Realized by 7 Hierarchical Porous NiGa₂O₄ Nanosheets

1 Received 00th January 20xx,
2 Accepted 00th January 20xx

3 DOI: 10.1039/x0xx00000x
4 www.rsc.org/

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9 and Seong Chan Jun^{a,*}

10 Rational design of composition and electrochemically favorable structure configuration of electrode materials
11 are highly required to develop high-performance supercapacitors. Here, we report our findings on the design
12 of interconnected NiGa₂O₄ nanosheets as advanced cathode electrodes for supercapacitors. Rietveld
13 refinement analysis demonstrates that the incorporation of Ga in NiO leads to a larger cubic lattice parameter
14 that promotes faster charge-transfer kinetics, enabling significantly improved electrochemical performance.
15 The NiGa₂O₄ electrode delivers a specific capacitance of 1508 F g⁻¹ at a current density of 1 A g⁻¹ with the
16 capacitance retention of 63.7% at 20 A g⁻¹, together with excellent cycling stability after 10000 charge–
17 discharge cycles (capacitance retention of 102.4%). An asymmetric supercapacitor device was assembled by
18 using NiGa₂O₄ and Fe₂O₃ as cathode and anode electrodes, respectively. The ASC delivers a high energy
19 density of 45.2 Wh kg⁻¹ at a power density of 1600 W kg⁻¹ with exceptional cycling stability (94.3% cell
20 capacitance retention after 10000 cycles). These results suggest that NiGa₂O₄ can serve as a new class cathode
21 material for advanced electrochemical energy storage applications.

22 1. Introduction

23 The ever-growing demands for high-power and high-energy
24 storage applications, such as portable electronic devices and
25 hybrid electric vehicles, have stimulated the urgent development
26 of supercapacitors with high energy density, high power density,
27 and long cycle life. Intensive research efforts have been
28 undertaken to develop nanostructured electrode materials to
29 improve electrochemical performance.^{1–3} Transition metal
30 oxides, which exhibit fast surface Faradaic redox reactions,
31 possess higher theoretical specific capacitances in comparison to
32 carbonaceous materials featuring reversible ion electrosorption
33 at the electrostatically charged electrode surface.^{4, 5} Among
34 these, Ni-based spinel materials with the general formula
35 NiM₂O₄ (M = Co, Mn, and Fe) have been intensively studied as

36 advanced cathode materials for supercapacitors, owing to their
37 high theoretical specific capacitance, environmental friendliness,
38 good chemical compatibility with nickel substrates, and rich redox
39 reaction property.^{6–10} Although energy densities have been greatly
40 improved in spinel-type Ni-based supercapacitors, the rate
41 capability and cycling stability accompanied by those
42 supercapacitors are typically low, owing to low electronic
43 conductivity and inferior mechanical/chemical stability.^{11, 12} To
44 date, incorporating suitable elements in pseudocapacitive electrode
45 materials has been regarded as an effective approach to tailor the
46 electrochemical performance of cathode electrode in the
47 supercapacitors. Therefore, the development of new class spinel
48 materials with desirable geometry should be explored. It came to
49 our attention that NiGa₂O₄ spinel structure with Ga trivalent
50 element has been widely studied in the areas of transparent
51 conduction oxide,¹⁰ optical absorption measurements,¹³ and
52 photocatalytic water splitting^{14–17} owing to its high stability, high
53 energy laser systems, and high photocatalytic activities. For
54 example, Ga dopant has been reported to increase the carrier
55 concentration, electron mobility, and electronic conductivity of
56 ZnO-based metal oxide, owing to highly degenerate Ga doping.¹⁸
57 ¹⁹ Zhou et al. reported that {111} surface of NaGa₂O₄
58 photocatalyst exhibits remarkable enhancement of the

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1 photocatalytic water splitting for H₂ and O₂ evolution due to
2 high mixed occupied Ga/Ni ratio compared to {100} facets.¹⁵
3 However, NiGa₂O₄ spinel structure has seldom been explored in
4 the field of energy storage. Until very recently, Zhang *et al.*,
5 pioneered a hydrothermal synthesis of Ga-doped NiO cathode
6 material for supercapacitor applications.²⁰ The results revealed
7 that Ga doping in NiO structure enabled a higher specific
8 capacitance and exceptional cycling stability compared to NiO,
9 signifying the importance of Ga doped Ni-based oxides for
10 potential application in supercapacitors. However, to the best of
11 author knowledge, the influence of Ga on the electrochemical
12 performance of Ni-based spinel structure was not reported and
13 fully understood. Therefore, in this study, we aim to understand
14 and unravel the role of Ga on the electrochemical performance
15 of a new class NiGa₂O₄ spinel structure as an advanced cathode
16 electrode for supercapacitors. To the best of our knowledge, the
17 role of Ga in improving the electrochemical performance of Ni-
18 Ga spinel materials for supercapacitors has not been reported
19 and is still unclear.

20 By contrast, despite the great progress of cathode materials, the
21 electrochemical performance of anode materials should be fully
22 considered to maximize the energy density and widen the
23 operation voltage window of asymmetric supercapacitor (ASC)
24 devices. Among these anode materials, hematite (Fe₂O₃) shows
25 superior electrochemical performance in the negative potential
26 owing to its high theoretical capacitance, low cost, and
27 nontoxicity.²¹ Significant efforts have been devoted to
28 improving the electrochemical performance of Fe₂O₃ by the use
29 of one-dimensional (1D) nanostructures, such as nanorods,²²
30 nanowires,²³ and nanotubes.²¹ The high specific capacitance and
31 enhanced cycling stability are attributed to the efficient transport
32 pathway between the electrons and ions. Thus, Fe₂O₃, with a
33 well-defined spindle structure, is anticipated to be a desirable
34 material for anode electrodes.

35 In this study, we investigate for the first time the mechanism of
36 Ga in a nickel gallate (NiGa₂O₄) spinel structure in enhancing
37 the specific capacitance, rate capability, and cycling durability,
38 reaching a specific capacitance of 1508 F g⁻¹, an increase of
39 95% with respect to the undoped NiO. We systematically
40 investigate a series of NiGa₂O₄ nanosheets hydrothermally
41 grown on Ni foam at different growth times (4, 8, 12, and 16 h).
42 An advanced ASC device was constructed on the basis of the
43 optimized hierarchical porous NiGa₂O₄ nanosheets at 12 h
44 (NiGa₂O₄-12 h) as the positive electrode and spindle-like Fe₂O₃
45 as the negative electrode. The ASC device exhibits a high cell
46 capacitance of 146 F g⁻¹ at 1 A g⁻¹, a maximum energy density

47 of 45.2 W h kg⁻¹ at a power density of 1600 W kg⁻¹, and
48 remarkable cycling stability with a retention of 94.3% specific
49 capacitance after 10,000 cycles. Rietveld refinement provides
50 solid evidence that the cubic lattice parameter *a* increases in
51 NiGa₂O₄, such that the diffusion coefficient of the OH⁻ ion and the
52 high rate capability of the material are significantly enhanced
53 compared to NiO nanosheets. In addition, Ga substitution shortens
54 the bond lengths of M-M and M-O (M represents Ni or Ga) as a
55 result of the smaller size of Ga³⁺ compared to Ni²⁺; this
56 phenomenon decreases the volume of the MO₆ octahedron,
57 thereby improving the structural stability and cycling stability.
58 Moreover, the electrical conductivity measurements prove that the
59 substitution of Ga³⁺ for Ni²⁺ improves the electronic conductivity
60 during the electrochemical reaction; consequently, a high rate
61 performance is obtained.

62 63 2. Experimental section

64 2.1. Material preparation

65 2.1.1. *Synthesis of NiGa₂O₄ nanosheets.* All chemicals were used
66 as received without further purification. Prior to deposition, a
67 piece of Ni foam (2 cm × 2 cm) was pretreated using 2 M HCl
68 solution with ultrasonication for 15 min; these samples were then
69 rinsed with acetone and deionized water to ensure a clean surface.
70 Typically, 1 mmol of Ni(NO₃)₂·6H₂O and 2 mmol of
71 Ga(NO₃)₃·xH₂O were dissolved in a mixed solvent of 80 mL
72 deionized water. Next, 1.44 g urea and 0.44 g NH₄F were slowly
73 added under continuous stirring. The pretreated Ni foam and the
74 obtained homogeneous solution was then transferred to a Teflon-
75 lined stainless-steel autoclave, which was sealed and maintained at
76 120 °C for different reaction times (4, 8, 12, and 16 h). After
77 cooling down to room temperature, the Ni substrates with as-
78 synthesized products were collected and rinsed with
79 ultrasonication to remove the loosely attached products on the
80 surface using deionized water and ethanol, followed by full drying
81 at 80 °C. Thereafter, the Ni substrates with as-grown NiGa-
82 precursors were calcined at 350 °C for 2 h with a temperature
83 ramp rate of 2 °C min⁻¹ in Ar atmosphere. The resulting NiGa₂O₄
84 with different hydrothermal times (4, 8, 12, and 16 h) were labeled
85 as NiGa₂O₄-4 h, NiGa₂O₄-8 h, NiGa₂O₄-12 h, and NiGa₂O₄-16 h.
86 The mass loadings of the aforementioned NiGa₂O₄ samples were
87 determined to be 1.0, 1.2, 1.3, and 1.3 mg cm⁻², respectively. In
88 the present synthesis scheme, the optimized NiGa₂O₄ nanosheets
89 were grown on different conductive substrates (Cu foam and
90 carbon fiber) via the same hydrothermal process; this method
91 proves that the process is general for various energy storage and
92 conversion applications. To illustrate the rationality of the present

1 work, we synthesized the NiO-12 h without the addition of Ga
2 precursor using a similar process.

3 *2.1.2. Synthesis of spindle-like Fe₂O₃.* For the synthesis of
4 spindle-like Fe₂O₃, 3 mM FeCl₃·6H₂O and 18 mM sodium
5 nitrate (NaNO₃) were dissolved in 80 mL water. Thereafter, the
6 obtained yellow solution was transferred into a 50 mL Teflon-
7 lined stainless-steel autoclave using a facile hydrothermal
8 process at 100 °C for 12 h; the solution was then dried at 60 °C
9 for 12 h. The prepared precursors were converted into Fe₂O₃ by
10 calcination at 450 °C in air for 2 h at a heating rate of 2 °C/min.

11

12 2.2. Material characterization

13 X-ray diffraction (XRD) patterns were collected using a Bruker
14 D8 Advanced X-Ray Diffractometer with Ni-filtered Cu K α
15 radiation ($\lambda = 1.5406 \text{ \AA}$) at a voltage of 40 kV and a current of
16 200 mA. The composition and valence states of the prepared
17 samples were analyzed by X-ray photoelectron spectroscopy
18 (XPS, VG Scientific ESCALAB250), which was calibrated to
19 the carbon peak C 1s at 284.6 eV. Field emission scanning
20 electron microscopy (FESEM) images were acquired using a
21 Hitachi S-4800. Transmission electron microscopy (TEM)
22 images were obtained using a Talos F200 X. Scanning
23 transmission electron microscopy with energy dispersive X-ray
24 spectroscopy (STEM-EDS; Talos F200 X) mapping was used to
25 identify the distributions of Ga, Ni, and O. The electrical
26 conductivity of the sample pellets was measured by a four-probe
27 machine (CMT-SR1000, AIT) at room temperature. The mass
28 loss determination was performed in Ar atmospheres with a
29 temperature ramp of 5 °C min⁻¹ using a TA instruments
30 apparatus (TGA Q50 V6.7 Build 203).

31 2.3. Electrochemical measurements

32 The electrochemical measurements were conducted in a three-
33 electrode electrochemical system containing a 6 M KOH
34 electrolyte at room temperature. The active material on Ni foam
35 (1 cm × 1 cm) was selected as the working electrode. Pt foil and
36 a saturated calomel electrode (SCE) were used as the counter
37 and reference electrodes, respectively. Cyclic voltammetry (CV)
38 and galvanostatic charge/discharge (GCD) were performed on
39 an Ivium-n-Stat electrochemical workstation (Ivium,
40 Netherlands). Electrochemical impedance spectrum
41 measurements were conducted in a frequency range of 100 kHz
42 to 0.1 Hz in the open circuit potential with an alternating current
43 perturbation of 5 mV.

44 ASCs were packaged in a CR 2302 coin cell; in this cell, a
45 NiGa₂O₄ nanosheet electrode, an Fe₂O₃ electrode, cellulose fabric,
46 and a 6 M KOH solution were used as the positive electrode,
47 negative electrode, separator, and electrolyte, respectively. The
48 negative electrode was prepared as follows: the prepared Fe₂O₃,
49 acetylene black, and polytetrafluoroethylene in the mass
50 proportions of 85:10:5 were mixed together by adding a small
51 amount of ethanol to produce a homogeneous mash. Then, the
52 resulting slurry was coated onto a Ni foam current collector with
53 mass loading of approximately 3 mg cm⁻². Finally, the fabricated
54 electrode was pressed and dried at 80 °C overnight, and was then
55 cut into a round film. The mass loading ratio of NiGa₂O₄
56 nanosheets to Fe₂O₃ was set to approximately 0.2 to obtain
57 optimized electrochemical performance. The specific capacitance
58 (C_{device}), energy density (E), and power density (P) were
59 calculated from the GCD curves according to the following
60 equations:^{24, 25}

$$61 C_{\text{device}} = \frac{I \times \Delta t}{\Delta V \times M} \quad (1)$$

$$62 E = \frac{1}{2} C_{\text{device}} \Delta V^2 \quad (2)$$

$$63 P = \frac{E}{\Delta t} \quad (3)$$

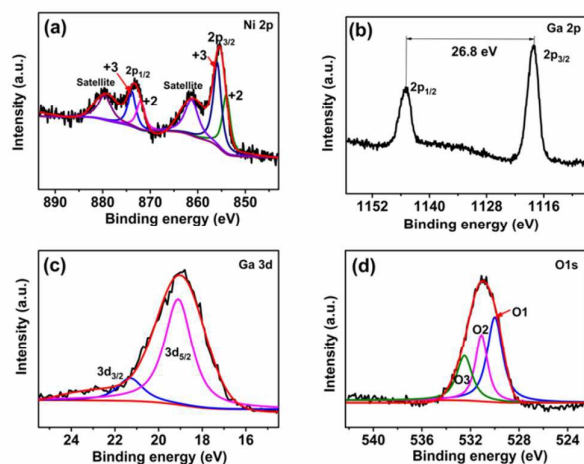
64 where I is the discharge current (mA), Δt is the discharge time (s),
65 M is the whole effective mass of the negative and positive
66 electrodes (mg), and ΔV is the operating potential window of the
67 device (V).

68

69 3. Results and discussion

70 The crystal structure of the NiGa-precursor was characterized by
71 XRD analysis (**Figure S1a**), which is in good agreement with the
72 NiGa-LDH reported in the literature.²⁶ The thermal behavior of
73 the pristine NiGa-precursor was examined by TGA techniques. As
74 shown in **Figure S1b**, the weight loss process can be divided into
75 two steps. The first step can be ascribed to the desorption of inter-
76 layered water and physically absorbed water, while the second
77 step corresponds to dehydroxylation of the layers and
78 decomposition of the carbonate anion.^{27, 28} The phases of the
79 NiGa₂O₄ and NiO were presented in **Figure S2**. The diffraction
80 peaks centered at $2\theta = 37.6^\circ$, 43.5° , and 63.2° can be assigned to
81 the (111), (200), and (220) crystal planes of NiO phase (JCPDS
82 no. 73-1519) with cubic structure and space group of $Fm-3m$ (No.
83 225). For the NiGa₂O₄, the diffraction peaks at 30.6° , 36.1° , 58.1° ,
84 and 63.6° are clearly identified, corresponding to the (220), (311),
85 (511), and (150) planes of the spinel NiGa₂O₄ phase (JCPDS card
86 no. 78-0546) with cubic structure and space group of $Fd-3m$ (No.
87 227). The broad reflection peaks observed in the patterns indicate
88 the small grain size of NiGa₂O₄. XPS measurements were

1 conducted to investigate the composition and surface electron
2 state of the porous NiGa₂O₄ nanosheets. The XPS full survey
3 spectrum of NiGa₂O₄ indicates the existence of Ni, Ga, and O
4 (Figure S3). The Ni/Ga atomic ratio for the prepared sample
5 determined by the XPS analysis is approximately 0.53, which
6 deviates slightly from the ratio of the reactants. This result may
7 be attributed to the higher permissible capability of Ni²⁺ ions to
8 precipitate in solution compared with Ga³⁺ ions. Using a
9 Gaussian fitting method, the Ni 2p emission spectrum (Figure
10 1a) can be fitted well with two prominent spin-orbit doublets,
11 characteristic of Ni oxidation states containing Ni²⁺ and Ni³⁺,
12 and two shakeup satellites at binding energies of 861.3 and
13 879.6 eV.^{29,30} The binding energy peaks at 854.0 and 872.0 eV
14 are ascribed to Ni²⁺, while the binding energy peaks at 855.9 and
15 873.9 eV correspond to Ni³⁺.³⁰ The Ga 2p spectrum (Figure 1b)
16 is fitted well with Ga 2p_{3/2} and Ga 2p_{1/2} peaks at 1118.1 and
17 1144.9 eV, respectively.³¹ The energy separation between the
18 two main peaks is approximately 26.8 eV, which is in
19 accordance with the reference value of 26.84 eV.³² Moreover,
20 two peaks located at 19.1 and 21.3 eV are observed from the
21 complex Ga 3d curve (Figure 1c).³¹ The O 1s spectrum (Figure
22 1d) is fitted by three peaks, marked by O1, O2, and O3. The O1
23 peak at 530.0 eV is indexed to typical metal-oxygen bonds; the
24 O2 contribution at 531.1 eV is attributed to the defect sites with
25 low oxygen coordination, contaminants, and surface species; the
26 O3 peak located at 532.5 eV is indexed to the multiplicity of
27 physisorbed/chemisorbed water at or near the surface.³³



28
29 **Figure 1.** XPS survey scan of (a) Ni 2p spectrum, (b) Ga
30 3d spectrum, and (d) O 1s regions.

31
32 The evolutionary stages of the as-prepared NiGa₂O₄ with
33 different hydrothermal reaction times (4, 8, 12, and 16 h) were
34 explored. After being hydrothermally processed for 4 h, the

35 interconnected nanosheet arrays with a transparent feature are
36 found densely packed and uniformly grown on the skeleton of the
37 NF substrate (Figures 2a and S4). When the reaction time is
38 extended to 8 h, the nanosheets evidently become thick (Figures
39 2b and S5). When the reaction time is increased to 12 h (Figures
40 2c and S6), well-aligned structures with the large nominal width
41 of these nanosheets are developed. The SEM image in Figure 2c
42 shows that the interlaced nanosheet subunits are approximately
43 700 nm in length, 20 nm in thickness, and vertically aligned on the
44 substrate, thereby forming a wall-like structure with possible good
45 mechanical strength. EDS mapping analysis shows the existence
46 of O, Ni, and Ga through the NiGa₂O₄-12 h nanosheets (Figure
47 S7). With the on-going reaction, a trace of chips agglomerated at
48 the surface of the corresponding products for 16 h is observed
49 (Figures 2d and S8); this phenomenon may lead to the
50 degradation of the electrochemical performance. Accordingly, we
51 focus our investigation on the products with the hydrothermal
52 reaction time of 12 h. As determined by the adsorption-desorption
53 isotherm (Figure S9), the hierarchical porous NiGa₂O₄-12 h
54 possesses a Brunauer-Emmett-Teller (BET) specific surface area
55 of approximately 158 m² g⁻¹, which is higher than those of
56 NiGa₂O₄-4 h (57 m² g⁻¹), NiGa₂O₄-8 h (96 m² g⁻¹), and NiGa₂O₄-
57 16 h (127 m² g⁻¹). The pore size distribution curves of NiGa₂O₄
58 samples reveal the mesoporous characteristics having the average
59 pore size ranges from 4.5 to 5.3 nm.

60 The high BET specific surface area and mesoporous structure are
61 beneficial to enrich the electroactive sites and shorten diffusion
62 paths for electrolyte ions; accordingly, the electrochemical
63 performance is enhanced. Hierarchical NiGa₂O₄ nanosheet arrays
64 supported on different types of conductive substrates (flexible
65 carbon fiber and Cu foam) are presented (Figure S10) to further
66 investigate the typical synthesis process for potential applications.
67 The existence of a Cu foam supporter was verified by EDS
68 mapping, as shown in Figure S11.

69

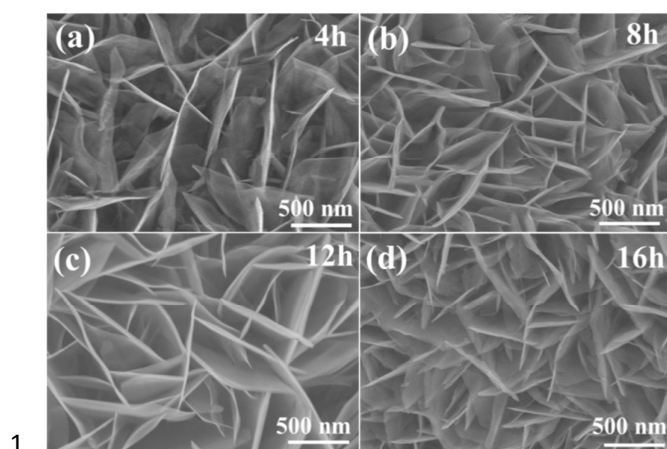


Figure 2. SEM images of the NiGa₂O₄ samples for different reaction times. (a) 4 h, (b) 8 h, (c) 12 h, and (d) 16 h.

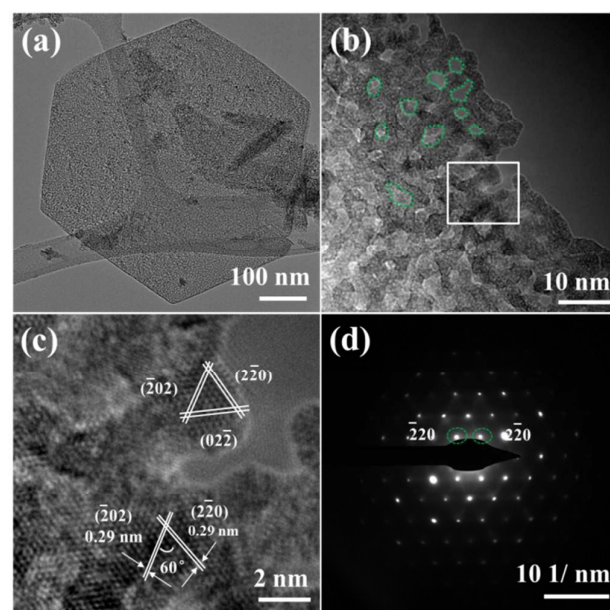


Figure 3. (a–b) TEM images, (c) HRTEM image of the selected area (white square) in (b), and (d) the corresponding SAED pattern of NiGa₂O₄-12 h.

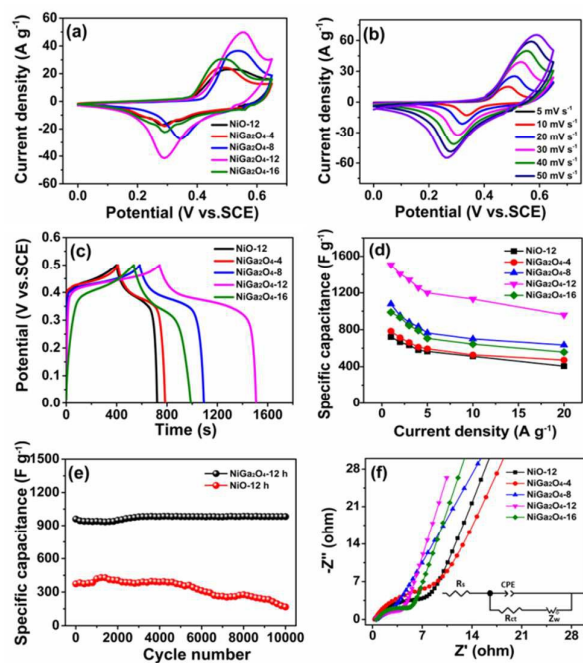
TEM clearly reveals a smooth nanosheet morphology (Figure 3a). Figure 3a shows a single typical nanoplate of NiGa₂O₄. The hexagonal shape is a first indication that the nanosheet is single crystalline. Figure 3b reveals numerous pores with an average diameter of ~3.5 nm, homogeneously distributed on the surface. The (220) crystal planes with an interlayer spacing of 0.29 nm were observed in the high-resolution TEM (HRTEM) image (Figure 3c). The spacing measured from the HRTEM is consistent with our XRD results (Figure S2). Furthermore, families of {220} planes with interfacial angles of 60° are observed. This indicates that the exposed in-plane crystal plane is the {111} facet. The corresponding selected area electron diffraction (SAED) pattern in Figure 3d, further confirms the monocrystal nature of the NiGa₂O₄ nanosheets.

Figure 4a shows the CV of pristine NiO-12 h and NiGa₂O₄ with different hydrothermal times (4, 8, 12, and 16 h) in 6 M KOH electrolyte at a scan rate of 30 mV s⁻¹. Visibly, a pair of well-defined redox peaks with anodic peaks at approximately 0.51 V vs. SCE and cathodic peaks around 0.31 V vs. SCE is observed for the as-prepared samples; these peaks originate mainly from the Faradaic redox reactions related to Ni-O/Ni-O-OH associated with OH⁻ anions in the electrolyte.³⁴ Notably, the pure NF substrate exhibits a negligible current compared with the as-fabricated samples (Figure S12); this finding shows that the capacitance contribution ratio from the NF (about 2.1% for NiGa₂O₄-12 h electrode) can be ignored. The area under the CV curve for the NiGa₂O₄ electrodes increases with the hydrothermal time, and it reaches a maximum for the NiGa₂O₄-12 h sample. However, the capacitance significantly decreases with further elongation of the hydrothermal time; this phenomenon may be ascribed to an excess deposition that leads to suppressed electrochemical activity. The CV curves of the NiGa₂O₄-12 h electrode with wide sweep rates ranging from 2 to 50 mV s⁻¹ were recorded in the potential window of 0–0.65 V vs. SCE in further exploring the current response of the NiGa₂O₄-12 h electrode (Figure 4b). The sweep rate gradually increases to 50 mV s⁻¹, and the shapes of the CV curves show essentially trifling changes with distinct current peaks; therefore, the electrode material has low resistance. The GCD measurements were performed at a current density of 1 A g⁻¹ (Figure 4c). As expected, the NiGa₂O₄-12 h electrode shows longer discharge times and thus higher specific capacitance than

1 the other electrodes. The obvious plateaus in the GCD curves
2 imply the existence of a Faradaic behavior, which is consistent
3 with the aforementioned CV results. GCD curves of the
4 NiGa₂O₄-12 h (**Figure S13**) at various current densities ranging
5 from 1 A g⁻¹ to 20 A g⁻¹ were obtained. The feature of the high
6 symmetrical GCD curves with a slight IR drop is manifested by
7 the low internal resistance and excellent electrochemical
8 reversibility of the NiGa₂O₄-12 h electrode.

9 The specific capacitances of the as-synthesized electrodes,
10 dependent on the discharge curves can be evaluated, as shown in
11 **Figure 4d**. The respective specific capacitances of the pristine
12 NiO-12 h and NiGa₂O₄ (4, 8, 12, and 16 h) electrodes are 722,
13 785, 1078, 1508, and 989 F g⁻¹ at a current density of 1 A g⁻¹.
14 The achieved specific capacitance of the NiGa₂O₄-12h electrode
15 is also comparable with those of the reported Ni bimetallic-
16 based electrodes, such as NiCo₂O₄ hollow spheres (1141 F g⁻¹ at
17 1 A g⁻¹),³⁵ hollow NiCo₂O₄ nanoarrays (1055.3 F g⁻¹ at 2.5 mA
18 cm⁻²),³⁶ copper–nickel oxide nanowires (1103.2 F g⁻¹ at 10 mA
19 cm⁻²),³⁷ and nickel–manganese oxide nanoparticles/multiwall
20 carbon nanotubes (803 F g⁻¹ at 1 mA cm⁻²).³⁸ When the current
21 density is increased by up to 20 A g⁻¹, the retentions of specific
22 capacitance values are 60.1%, 58.8%, 63.7%, and 56.4% for
23 NiGa₂O₄ (4, 8, 12, and 16 h); these values are superior to those
24 for pristine NiO-12 h (56.3%). The high rate capacities are also
25 higher than the reported Ni-based electrodes, such as NiO
26 nanoflowers (52.5% from 0.5 A g⁻¹ to 5 A g⁻¹),³⁹ CNT/NiO
27 nanosheets (50.2% from 1 A g⁻¹ to 20 A g⁻¹),⁴⁰ and
28 NiCo₂O₄@MnO₂ core–shell nanowires (50.2% from 2 mA cm⁻²
29 to 20 mA cm⁻²).⁴¹ The long-term cycling life at a high current
30 density is a critical parameter for SCs to address the desired
31 demands for commercial applications. **Figure 4e** shows that
32 NiGa₂O₄-12 h delivers a high specific capacitance of 983 F g⁻¹
33 after 10000 cycles, corresponding to a high capacitance
34 retention of 102.4% at a high current density of 20 A g⁻¹; this
35 value is obviously higher than that for NiO-12 h (44.9%
36 capacitance retention). The prolonged cycling test is considered
37 superior to those for Ni-based oxides/hydroxides/sulfides (**Table**
38 **S1**). Electrochemical impedance spectroscopy curves of the
39 samples were recorded in analyzing the electrical conductivity
40 and dynamical characteristics of the electrodes.⁴² The
41 corresponding Nyquist spectra can be fitted with an equivalent
42 circuit (**inset of Figure 4f**). The partial semicircle represents the
43 interfacial charge transfer resistance (*R*_{ct}). As shown in **Figure**
44 **4f**, the *R*_{ct} values of the NiO-12 h and NiGa₂O₄ with different
45 hydrothermal times (4, 8, 12, and 16 h) are 7.9, 10.4, 5.9, 5.5,
46 and 6.3 Ω, respectively. Compared with the other electrodes, the

47 low *R*_{ct} of NiGa₂O₄-12 h electrode tends to achieve a high charge
48 transfer efficiency.⁴² As observed in **Figure S14**, the *R*_{ct} values of
49 NiO-12 h and NiGa₂O₄-12 h slightly increase after the cycling test,
50 which indicates that the NiGa₂O₄-12 h sample retains desirable
51 interfacial charge transfer resistances and good cycling stability
52 compared to NiO-12 h sample.



53 **Figure 4.** (a) CV curves of the NiO-12 h and NiGa₂O₄ (4, 8, 12, and 16 h). (b)
54 CV curves of NiGa₂O₄-12 h at various scan rates from 5 mV s⁻¹ to 50 mV s⁻¹;
55 (c) GCD curves of the NiO-12 h and NiGa₂O₄ (4, 8, 12, and 16 h). (d) Specific
56 capacitance dependent on current densities of electrodes; (e) cycling
57 performance of the NiO-12 h and NiGa₂O₄-12 h at a current density of 20 A
58 g⁻¹; and (f) Nyquist plots of these electrodes fitted with the corresponding
59 equivalent circuit.

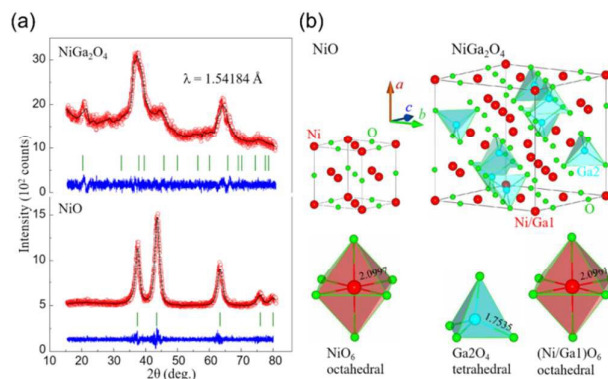
60 The exceptional supercapacitive performance can be attributed to
61 the following facts: The ultrathin feature of nanosheets can shorten
62 the OH⁻ ion diffusion distance and electron transportation path,
63 thereby resulting in the high utilization of electroactive species;
64 the void space between the nanosheets can effectively facilitate the
65 penetration of electrolyte ions and accommodate the volume
66 variation during continuous charge–discharge cycling;
67 mechanically stable self-assembly without the addition of binders
68 ensures favorable kinetics in electron/ion transportation.

69 SEM and TEM images were obtained after cycling to investigate
70 the origin of the long-term stability of the NiGa₂O₄-12 h electrode.
71 After the cycling test, the electrode still maintains good structural
72 integrity. However, numerous petal-like layers form uniformly on
73 the surface of the NiGa₂O₄ nanosheets (**Figures S15a–b**). The
74 mechanical robustness feature is particularly beneficial for highly
75

1 exposed surface areas in efficiently increasing the utilization
 2 efficiency of active materials. A typical TEM image (**Figure**
 3 **S15c**) shows that the nanosheet surface is enclosed by folded
 4 layers. A magnified TEM image, shown in **Figure S15d**,
 5 displays the nanosheets comprising small nanoparticles and
 6 featuring numerous nanopores; these features allow the
 7 electrolyte ions to access and transport along the inner surface of
 8 the active materials efficiently. These results support the
 9 potential of NiGa₂O₄ nanosheets as electrodes for SCs with
 10 superior cycling performance.

11 We attempt to explore the role of Ga in improving the high rate
 12 capability and cycling performance of the newly explored
 13 NiGa₂O₄ spinel structure for SCs. Rietveld refinement using
 14 XRD data was analyzed. **Figure 5a** shows the Rietveld
 15 refinement results of the as-synthesized samples hydrothermally
 16 grown for 12 h (NiGa₂O₄-12 and NiO-12). The refined crystal
 17 structure of NiGa₂O₄ is shown in **Figure 5b**. The spinel
 18 NiGa₂O₄ adopts the structure with Ni²⁺ and Ga³⁺ cations
 19 occupying tetrahedral and octahedral sites. The lattice parameter
 20 values are calculated from the refinements and are found to be a
 21 = 4.1921(15) Å and 8.2977(81) Å for NiO and NiGa₂O₄,
 22 respectively (**Table S2**). Our Rietveld refinements show that the
 23 lattice parameter a is increased in NiGa₂O₄ compared with that
 24 in NiO; this finding indicates that the diffusion coefficient of the
 25 OH⁻ ions is enhanced, as well as the high rate capability of the
 26 material. Gao *et al.* applied density functional theory to
 27 investigate the binding energy of Li-rich Mn-based cathode
 28 materials; they concluded that a short bond length usually means
 29 a high binding energy, indicating the high stability of the crystal
 30 structure.⁴³ Our results show that the length of the Ga-Ga bonds
 31 in NiGa₂O₄ is significantly shorter than that of the Ni-Ni bonds
 32 in NiO, as a result of the smaller ionic size of Ga³⁺ (0.61 Å,
 33 coordination number: 4; 0.76 Å, coordination number: 6)
 34 compared to Ni²⁺ (0.83 Å, coordination number: 6); this finding
 35 indicates that NiGa₂O₄ has a higher structural and cycling
 36 stability of the crystal structure compared with the compound
 37 NiO. Moreover, the aliovalent substitution of Ga³⁺ for Ni²⁺
 38 improves the electronic conductivity during electrochemical
 39 reactions, such that a high rate performance is obtained. The
 40 measured electrical conductivity of NiGa₂O₄ is 2.44×10^{-3} S
 41 m⁻¹ compared to that of NiO (2.62×10^{-4} S m⁻¹), which verifies
 42 the contribution to the enhanced electrical conductivity by the
 43 aliovalent substitution of Ga³⁺ for Ni²⁺. In addition, the spinel
 44 NiGa₂O₄ adopts the structure ($Fd-3m$ space group) with Ni²⁺ and
 45 Ga³⁺ cations located in the center of O₄ tetrahedrons (Ga³⁺) and
 46 O₆ octahedra (Ni²⁺ and Ga³⁺), respectively.⁴⁴ Such edge-sharing

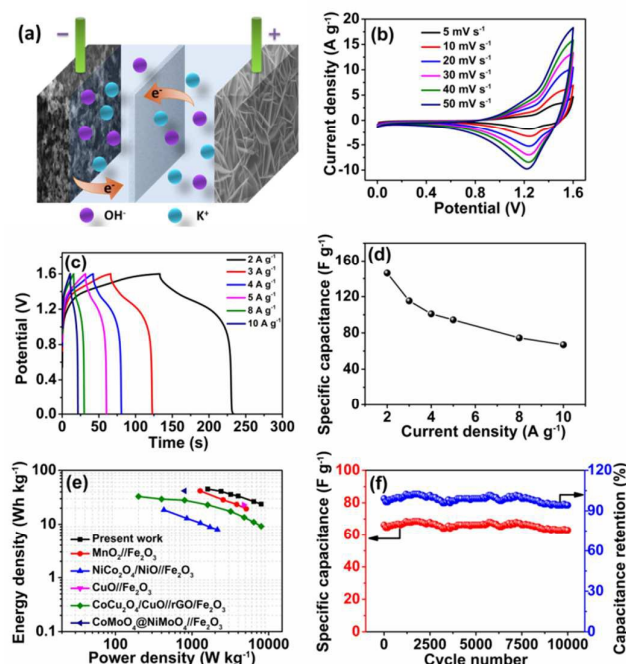
47 octahedra established a three-dimensional network of tunnels that
 48 accounts for the efficient ion diffusion.⁴⁵



49 **Figure 5.** (a) Rietveld refinement patterns of XRD data for the NiO and
 50 NiGa₂O₄. (b) Crystal structures (with one unit cell shown as solid lines) and
 51 their building blocks of NiO ($Fm-3m$) and NiGa₂O₄ ($Fd-3m$). The building
 52 blocks are NiO₆ octahedral for NiO, and Ga₂O₄ tetrahedral and (Ni/Ga)₆
 53 octahedral for NiGa₂O₄. The corresponding shortest bond lengths of Ni-O (in
 54 NiO) and Ni(Ga1)-O and Ga2-O are marked in units of Å.

55
 56 The XRD pattern of the as-synthesized Fe₂O₃ was obtained
 57 (**Figure S16a**). All the diffraction peaks can be indexed to the
 58 rhombohedral-type Fe₂O₃ phase (JCPDS Card no. 1-1053).⁴⁶
 59 **Figure S16b** shows that Fe₂O₃ is composed of a large number of
 60 highly monodispersed spindle-like subunits. The subunits with
 61 smooth surfaces have a length of approximately 120 nm. Notably,
 62 numerous mesopores are uniformly distributed throughout the
 63 entire surface of the subunits; this phenomenon may be attributed
 64 mainly to the re-crystallization process and gas release during the
 65 calcination process.⁴⁷ TEM observations (**Figure S16c**) show that
 66 the spindle-like subunits comprise numerous large void spaces
 67 with sizes in the range of 20–30 nm; this finding is consistent with
 68 the SEM result. **Figure S16d** shows the lattice fringe with an
 69 interplanar spacing of 0.17 nm, which can be indexed to the (116)
 70 plane of the Fe₂O₃ phase. EDX spectroscopy data confirm the
 71 existence of Fe and O in the subunits (**Figure S17**). The CV
 72 curves of the Fe₂O₃ electrode at various scan rates ranging from 5
 73 to 100 mV s⁻¹ in the potential window of -0.9–0 V vs. SCE
 74 (**Figure S18a**). The similar rectangular shape of the CV curves is
 75 manifested by the Faradaic behavior of Fe₂O₃; this characteristic
 76 may arise from a reversible Fe³⁺/Fe²⁺ coupling. The peak current
 77 increases with an insignificant change in the CV shape, although
 78 the scan rate increases to 100 mV s⁻¹; thus, the good
 79 electrochemical reversibility and high rate capability of the
 80 material is revealed. GCD measurements were conducted at
 81 various current densities ranging from 1 to 30 A g⁻¹ (**Figure**
 82 **S18b**). The specific capacitance corresponds to 171.5 F g⁻¹ at a
 83 current density of 1 A g⁻¹, and it remains at 86.7 F g⁻¹ at a high

1 current density of 30 A g^{-1} (Figure S18c). In particular, the
 2 stable specific capacitance of 103 F g^{-1} can be retained for Fe_2O_3
 3 after 5,000 cycles at 10 A g^{-1} with a capacitance retention of
 4 nearly 86% (Figure S18d); this performance indicates a good
 5 electrochemical stability. The outstanding rate capability and
 6 electrochemical stability can be attributed to the 1D spindle
 7 structure, which is conducive to fast ion diffusion and provides a
 8 short transport distance. To confirm the excellent performance
 9 of the spindle-like Fe_2O_3 electrode, the CV curves of the ASC
 10 device (Figure 6b) were collected at different scan rates ranging
 11 from 5 to 50 mV s^{-1} ; these curves exhibit a sloped shape,
 12 indicating the contribution of Faradic capacitance from the ASC
 13 device.⁴⁸ A slight distortion is observed for the CV curves
 14 conducted at high scan rates, suggesting a good rate capability.
 15 GCD curves at different current densities with the potential
 16 window of 1.6 V are shown in Figure 6c. The nonlinear charge–
 17 discharge profiles demonstrate the Faradic behavior of the
 18 electrode.⁴⁹ The specific capacitance as a function of the
 19 discharge current density is plotted in Figure 6d. The
 20 capacitances based on the total mass can be calculated as 127,
 21 115, 101, 94, 75, and 67 F g^{-1} at the current densities of 2, 3, 4,
 22 5, 8, and 10 A g^{-1} , respectively. The leakage current and self-
 23 discharge characteristics of supercapacitor device are two
 24 parameters essential to evaluating its practical performance. As
 25 shown in Figure S19, the leakage current of the constructed
 26 $\text{NiGa}_2\text{O}_4/\text{Fe}_2\text{O}_3$ ASC device rapidly decreases at first and then
 27 stabilizes at $39 \mu\text{A}$ after maintaining a constant voltage for 2 h.
 28 The output voltage reaches around 0.94 V after 24 h, which
 29 demonstrates good energy storage performance and high
 30 stability of the ASC device. The Ragone plot of the
 31 $\text{NiGa}_2\text{O}_4/\text{Fe}_2\text{O}_3$ ASC device derived from the discharge curves
 32 is shown in Figure 6e. An energy density of 45.2 Wh kg^{-1} can
 33 be achieved at a power density of $1,600 \text{ W kg}^{-1}$, and it remains
 34 at 23.8 Wh kg^{-1} , even at a high power density of $8,000 \text{ W kg}^{-1}$;
 35 these values are advantageous over those for previously reported
 36 devices.^{50–54} Figure 6f shows the cycling performance of the
 37 ASC device measured at a current density of 10 A g^{-1} up to
 38 10,000 cycles. Notably, the ASC device delivers an outstanding
 39 capacitance retention of 94.3% after the cycling test. Such
 40 cycling performance is highly competitive with those of
 41 previous reports (Table S3). This can be attributed to a large
 42 number of electrochemical active sites of the NiGa_2O_4
 43 nanosheets, as well as the facile access and fast diffusion path
 44 provided by the spindle-like Fe_2O_3 .



45
 46 **Figure 6.** (a) Schematic of the NiGa_2O_4 -12 h/ Fe_2O_3 ASC device. (b) CV curves
 47 at different scan rates from 5 mV s^{-1} to 50 mV s^{-1} ; (c) GCD curves in the
 48 potential range from 0 V to 1.6 V; (d) specific capacitance versus current
 49 density; (e) Ragone plots; and (f) cyclic stability at 10 A g^{-1} .

50

51 4. Conclusions

52 In summary, we have successfully developed new spinel-type
 53 porous NiGa_2O_4 nanosheets by a facile method. The Rietveld
 54 refinement reveals that the increased structure stability and
 55 improved ion diffusion kinetics of the NiGa_2O_4 electrodes arise
 56 from the aliovalent substitution of Ga^{3+} for Ni^{2+} in the spinel
 57 structure. Given the large exposed active surface of its hierarchical
 58 nanoscale porous structure and chemically stable interface, the
 59 NiGa_2O_4 electrode exhibits a high specific capacitance of 1508 F g^{-1}
 60 at a current density of 1 A g^{-1} , a good rate capability (63.7%
 61 retention at 20 A g^{-1}), and an excellent cycling stability of 102.4%
 62 retention after 10,000 cycles. More remarkably, the
 63 $\text{NiGa}_2\text{O}_4/\text{Fe}_2\text{O}_3$ ASC device delivers a high energy density of
 64 45.2 Wh kg^{-1} at a power density of 1600 W kg^{-1} . Furthermore, the
 65 device exhibits exceptional cycling stability, with approximately
 66 94.3% cell capacitance retention after 10000 cycles. All these
 67 results indicate that the aliovalent substitution between different
 68 cations and efficient structural design presented here could pave
 69 the way for other electrochemical systems.

70

71 Acknowledgements

- 1 This work was supported by the Science and Technology
2 Development Fund from Macau SAR (FDCT-098/2015/A3), the
3 Start-up Research Grant (SRG2015-00057-FST) from Research
4 & Development Office at University of Macau, UEA funding,
5 and the Korean Government (MSIP) (No. 2015R1A5A1037668)
6 through the National Research Foundation of Korea (NRF)
7 funded by the Ministry of Education, Science, and Technology
8 (MEST).
9
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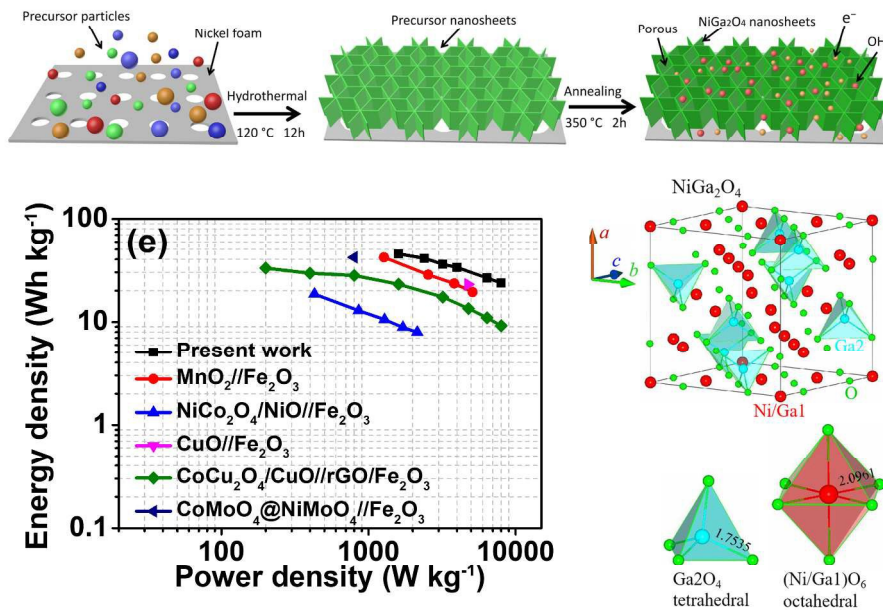
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